

勝特力電材超市-龍山店 886-3-5773766
 勝特力電材超市-光復店 886-3-5729570
 勝特力電子(上海) 86-21-34970699
 勝特力電子(深圳) 86-755-83298787
<http://www.100y.com.tw>

IRF7455PbF

SMPS MOSFET

HEXFET[®] Power MOSFET

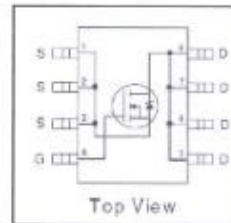
Applications

- High Frequency DC-DC Converters with Synchronous Rectification
- Lead-Free

V_{DSS}	$R_{DS(on) \max}$	I_D
30V	0.0075 Ω	15A

Benefits

- Ultra-Low $R_{DS(on)}$ at 4.5V V_{GS}
- Low Charge and Low Gate Impedance to Reduce Switching Losses
- Fully Characterized Avalanche Voltage and Current



Absolute Maximum Ratings

Symbol	Parameter	Max.	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-to-Source Voltage	± 12	V
$I_D @ T_A = 25^\circ\text{C}$	Continuous Drain Current, $V_{DS} @ 10\text{V}$	15	A
$I_D @ T_A = 70^\circ\text{C}$	Continuous Drain Current, $V_{DS} @ 10\text{V}$	12	
I_{DM}	Pulsed Drain Current ^①	120	
$P_D @ T_A = 25^\circ\text{C}$	Maximum Power Dissipation ^③	2.5	W
$P_D @ T_A = 70^\circ\text{C}$	Maximum Power Dissipation ^③	1.6	W
	Linear Derating Factor	0.02	W/ $^\circ\text{C}$
T_J, T_{STG}	Junction and Storage Temperature Range	-55 to +150	$^\circ\text{C}$

Thermal Resistance

	Parameter	Max.	Units
$R_{\theta JA}$	Maximum Junction-to-Ambient ^④	50	$^\circ\text{C/W}$

Typical SMPS Topologies

- Telecom 48V Input Converters with Logic-Level Driven Synchronous Rectifiers

Notes ^① through ^④ are on page 8

Static @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V _{BR(DSS)}	Drain-to-Source Breakdown Voltage	30	—	—	V	V _{GS} = 0V, I _D = 250μA
ΔV _{BR(DSS)/ΔT_J}	Breakdown Voltage Temp. Coefficient	—	0.029	—	V/°C	Reference to 25°C, I _D = 1mA
R _{DS(on)}	Static Drain-to-Source On-Resistance	—	0.0090	0.0075	Ω	V _{GS} = 10V, I _D = 15A ①
		—	0.0069	0.009		V _{GS} = 4.5V, I _D = 12A ②
		—	0.010	0.020		V _{GS} = 2.8V, I _D = 3.5A ③
V _{GS(th)}	Gate Threshold Voltage	0.6	—	2.0	V	V _{DS} = V _{GS} , I _D = 250μA
I _{DSS}	Drain-to-Source Leakage Current	—	—	20	μA	V _{DS} = 24V, V _{GS} = 0V
		—	—	100		V _{DS} = 24V, V _{GS} = 0V, T _J = 125°C
I _{GSS}	Gate-to-Source Forward Leakage	—	—	200	nA	V _{GS} = 12V
	Gate-to-Source Reverse Leakage	—	—	-200		V _{GS} = -12V


Dynamic @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
g _{fs}	Forward Transconductance	44	—	—	S	V _{GS} = 10V, I _D = 15A
Q _g	Total Gate Charge	—	37	58	nC	I _D = 15A
Q _{gs}	Gate-to-Source Charge	—	8.9	13		V _{DS} = 24V
Q _{gd}	Gate-to-Drain ("Miller") Charge	—	13	20		V _{GS} = 5.0V, ④
t _{d(on)}	Turn-On Delay Time	—	17	—	ns	V _{DD} = 15V
t _r	Rise Time	—	18	—		I _D = 1.0A
t _{d(off)}	Turn-Off Delay Time	—	51	—		R _θ = 6.0Ω
t _f	Fall Time	—	44	—		V _{GS} = 4.5V ④
C _{iss}	Input Capacitance	—	3480	—		V _{GS} = 0V
C _{oss}	Output Capacitance	—	870	—	pF	V _{DS} = 25V
C _{rss}	Reverse Transfer Capacitance	—	100	—		f = 1.0MHz

Avalanche Characteristics

	Parameter	Typ.	Max.	Units
E _{AS}	Single Pulse Avalanche Energy②	—	200	mJ
I _{AR}	Avalanche Current③	—	15	A
E _{AR}	Repetitive Avalanche Energy①	—	0.25	mJ

Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I _S	Continuous Source Current (Body Diode)	—	—	2.5	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I _{SM}	Pulsed Source Current (Body Diode) ①	—	—	120		
V _{SD}	Diode Forward Voltage	—	—	1.2	V	T _J = 25°C, I _S = 2.5A, V _{GS} = 0V ④
t _{rr}	Reverse Recovery Time	—	64	96	ns	T _J = 25°C, I _F = 2.5A
Q _{rr}	Reverse Recovery Charge	—	99	150	nC	di/dt = 100A/μs ④

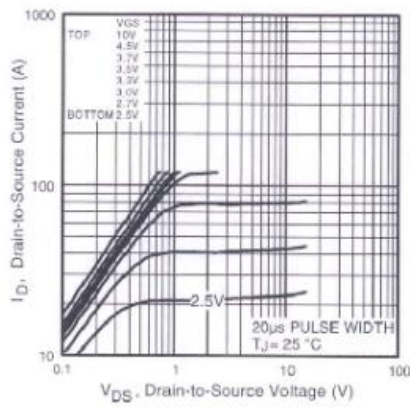


Fig 1. Typical Output Characteristics

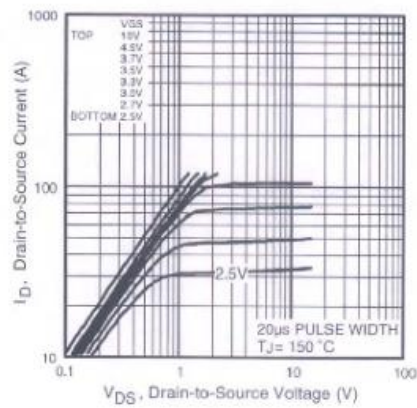


Fig 2. Typical Output Characteristics

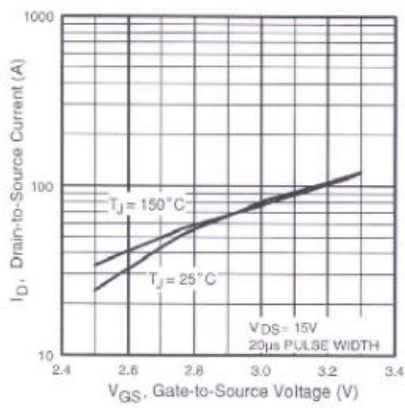


Fig 3. Typical Transfer Characteristics

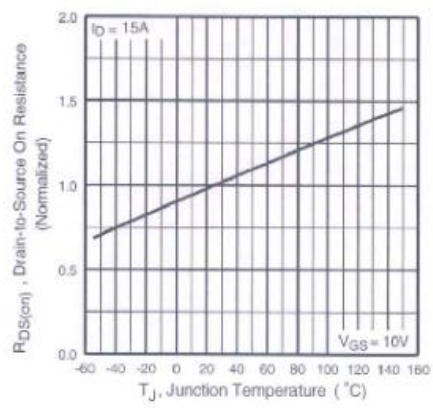


Fig 4. Normalized On-Resistance Vs. Temperature

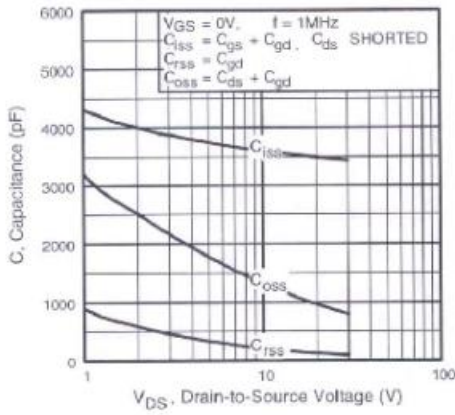


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

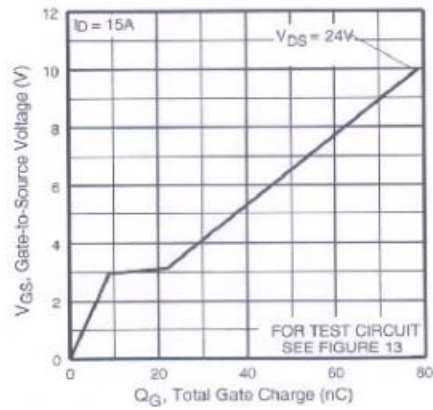


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

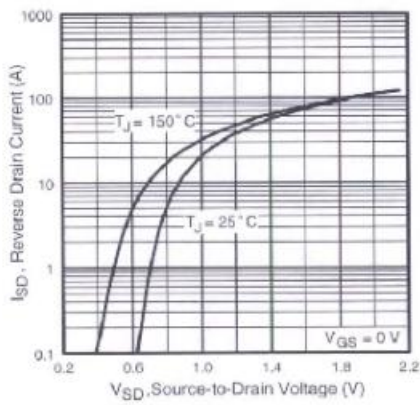


Fig 7. Typical Source-Drain Diode Forward Voltage

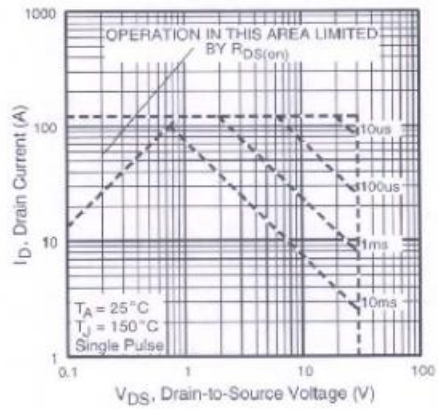


Fig 8. Maximum Safe Operating Area

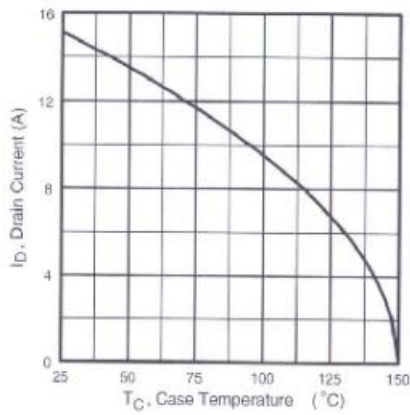


Fig 9. Maximum Drain Current Vs. Case Temperature

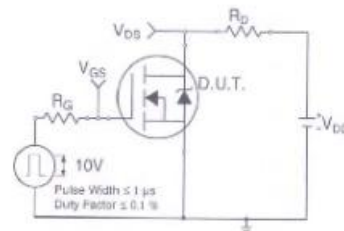


Fig 10a. Switching Time Test Circuit

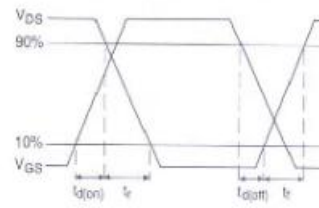


Fig 10b. Switching Time Waveforms

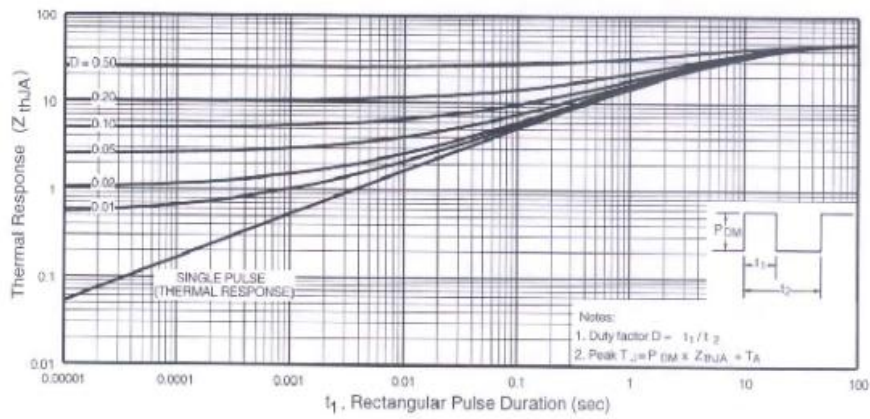


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

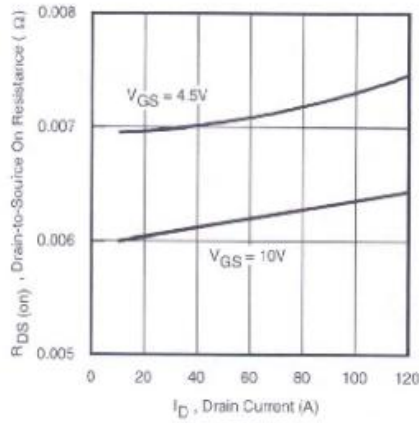


Fig 12. On-Resistance Vs. Drain Current

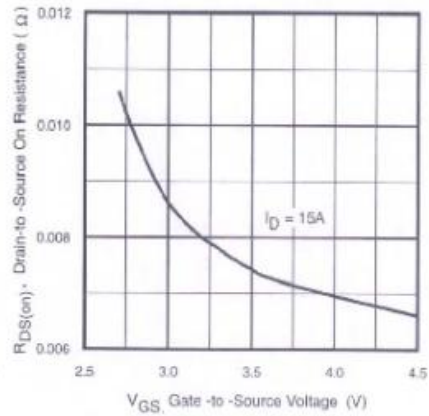


Fig 13. On-Resistance Vs. Gate Voltage

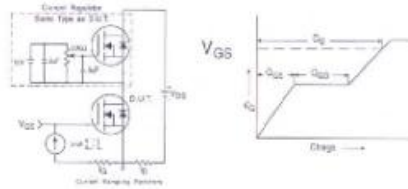


Fig 13a&b. Basic Gate Charge Test Circuit and Waveform

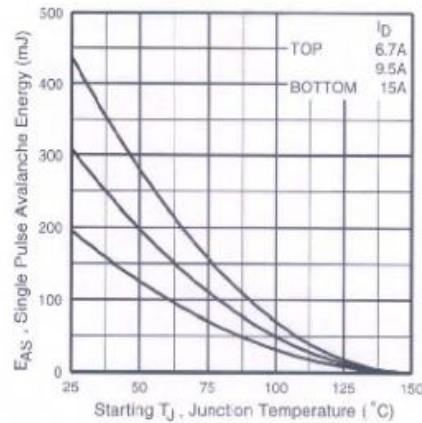


Fig 14c. Maximum Avalanche Energy Vs. Drain Current

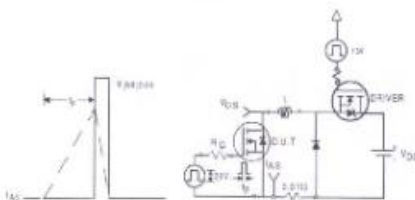
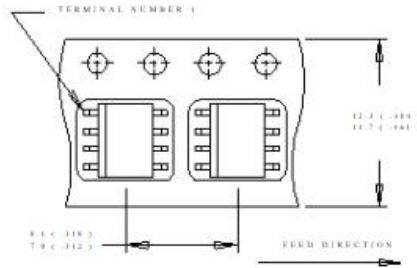


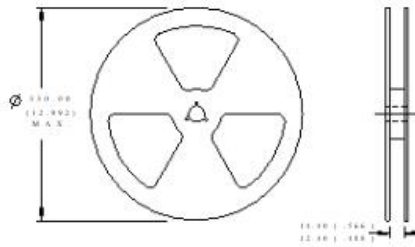
Fig 14a&b. Unclamped Inductive Test circuit and Waveforms

SO-8 Tape and Reel

Dimensions are shown in millimeters (inches)



- NOTES:
 1. CONTROLLING DIMENSION - MILLIMETER.
 2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
 3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



- NOTES:
 1. CONTROLLING DIMENSION - MILLIMETER.
 2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

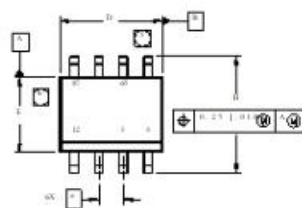
Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting $T_J = 25^\circ\text{C}$, $L = 1.8\text{mH}$, $R_G = 25\Omega$, $I_{AS} = 15\text{A}$.
- ③ Pulse width $\leq 300\mu\text{s}$; duty cycle $\leq 2\%$.
- ④ When mounted on 1 inch square copper board, $t < 10$ sec

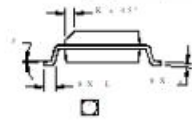
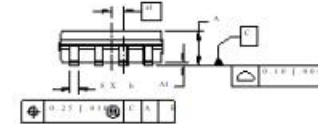
Data and specifications subject to change without notice.
 This product has been designed and qualified for the Consumer market.
 Qualifications Standards can be found on IR's Web site.

SO-8 Package Outline

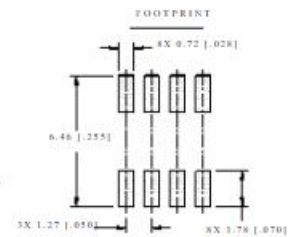
Dimensions are shown in millimeters (inches)



	INCHES		MILLIMETERS	
SYMBOL	MIN	MAX	MIN	MAX
A	0.175	0.200	4.43	5.08
B	0.015	0.025	0.38	0.64
C	0.015	0.025	0.38	0.64
D	0.015	0.025	0.38	0.64
E	0.015	0.025	0.38	0.64
F	0.015	0.025	0.38	0.64
G	0.015	0.025	0.38	0.64
H	0.015	0.025	0.38	0.64
I	0.015	0.025	0.38	0.64
J	0.015	0.025	0.38	0.64
K	0.015	0.025	0.38	0.64
L	0.015	0.025	0.38	0.64
M	0.015	0.025	0.38	0.64
N	0.015	0.025	0.38	0.64
O	0.015	0.025	0.38	0.64
P	0.015	0.025	0.38	0.64
Q	0.015	0.025	0.38	0.64
R	0.015	0.025	0.38	0.64
S	0.015	0.025	0.38	0.64
T	0.015	0.025	0.38	0.64
U	0.015	0.025	0.38	0.64
V	0.015	0.025	0.38	0.64
W	0.015	0.025	0.38	0.64
X	0.015	0.025	0.38	0.64
Y	0.015	0.025	0.38	0.64
Z	0.015	0.025	0.38	0.64



- NOTES:
1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
 4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
- ① DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.15 (0.006).
 - ② DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.25 (0.010).
 - ③ DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE.



SO-8 Part Marking Information (Lead-Free)

EXAMPLE: THIS IS AN IRF7101 (MOSFET)

